

Silicon NPN Power Transistors

2SC2305

DESCRIPTION

- With TO-3PN package
- High breakdown voltage
- Fast switching speed
- Wide safe operating area

APPLICATIONS

- For switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

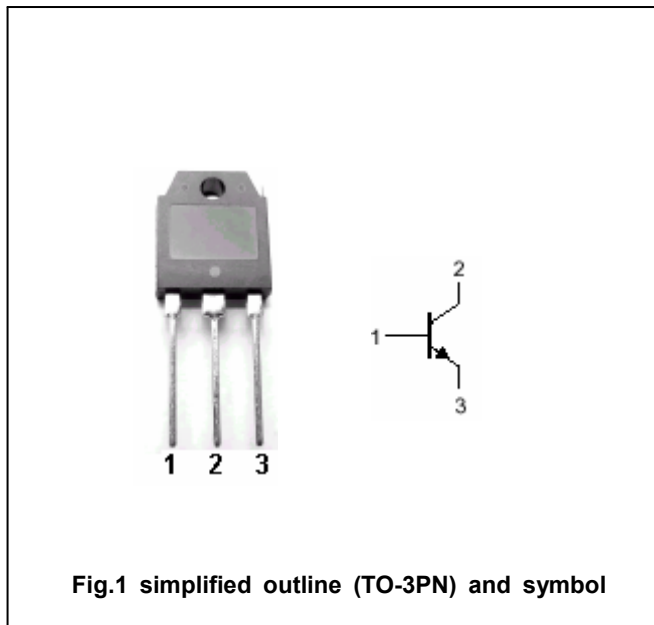


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	400	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	8	V
I _C	Collector current (DC)		7	A
I _{CM}	Collector current-peak		14	A
I _B	Base current (DC)		3	A
P _C	Collector power dissipation	T _C =25°C	80	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon NPN Power Transistors

2SC2305

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA ; R_{BE}=\infty$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A ; I_B=0.8A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4A ; I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=400V ; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			10	μA
h_{FE-1}	DC current gain	$I_C=0.8A ; V_{CE}=5V$	15		50	
h_{FE-2}	DC current gain	$I_C=4A ; V_{CE}=5V$	10			

Silicon NPN Power Transistors

2SC2305

PACKAGE OUTLINE

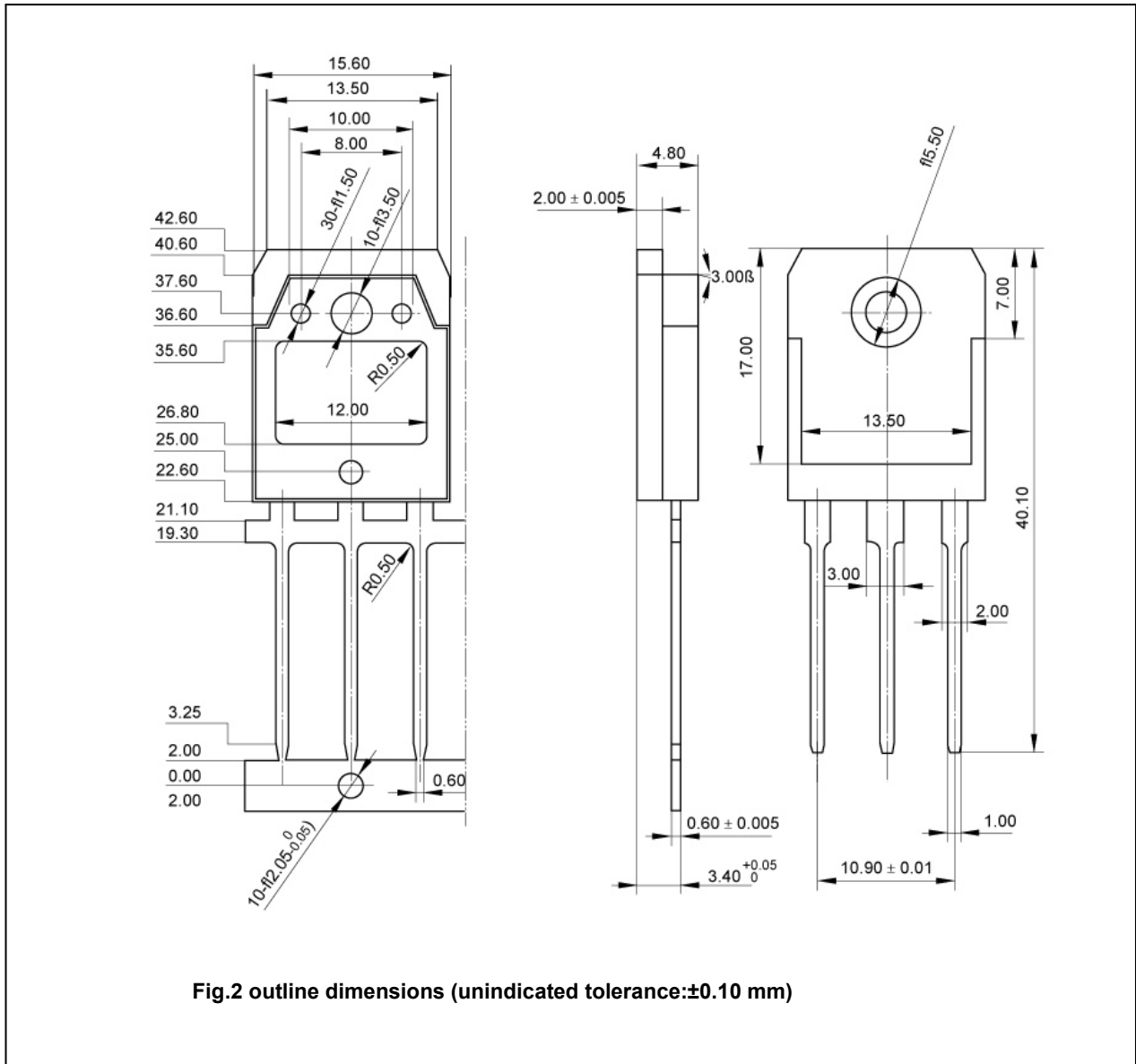


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)